

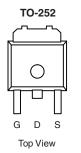
220N06L-VB Datasheet N-Channel 60-V (D-S) MOSFET

PRODUCT	SUMMARY				
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A) ^a			
60	0.025 at V _{GS} = 10 V	45			
30	0.030 at V _{GS} = 4.5 V	40			

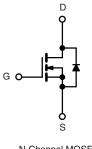
FEATURES

- Trench Power MOSFET
- 175 °C Junction Temperature





Drain Connected to Tab



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _C =	25 °C, unless othe	rwise noted			
Parameter		Symbol	Limit	Unit	
Gate-Source Voltage	V _{GS}	± 20	V		
Continuous Droin Current /T 175 °CV	T _C = 25 °C	L	45		
Continuous Drain Current $(T_J = 175 \ ^{\circ}C)^{b}$	T _C = 100 °C	I _D	35		
Pulsed Drain Current		I _{DM}	100	A	
Continuous Source Current (Diode Conduction)		۱ _S	23		
Avalanche Current		I _{AS}	20	1	
Single Avalanche Energy (Duty Cycle \leq 1 %)	L = 0.1 mH	E _{AS}	20	mJ	
Maximum Davier Diasin stiller	T _C = 25 °C	Р	100	14/	
Maximum Power Dissipation	T _A = 25 °C	P _D	3 ^a	W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \le 10 \text{ sec}$	R _{thJA}	18	22	
Maximum Junction-to-Ambient*	Steady State	¹ 'thJA	40	50	°C/W
Maximum Junction-to-Case		R _{thJC}	3.2	4	

Notes:

a. Surface Mounted on 1" x 1" FR4 board, t \leq 10 sec.

SPECIFICATIONS $T_J = 25$	°C, unless o	otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ ^a	Max	Unit		
Static								
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 V, I_D = 250 \mu A$	60			М		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1.0	2.0	3.0	Unit V nA μA A Ω S PF nC nS		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA		
		$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1			
ero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$			50	μΑ		
		$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$			250			
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = 5 V, V_{GS} = 10 V$	50			А		
h		V _{GS} = 10 V, I _D = 15 A		0.025		μΑ Α Ω S		
		V_{GS} = 10 V, I _D = 15 A, T _J = 125 °C		0.055				
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 10 V, I _D = 15 A, T _J = 175 °C		0.069		Ω		
		V _{GS} = 4.5 V, I _D = 10 A		0.030				
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 15 A		20		S		
Dynamic ^a	•							
Input Capacitance	C _{iss}			1500				
Output Capacitance	C _{oss}	$V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz$		140		pF		
Reverse Transfer Capacitance	C _{rss}			60		1		
Total Gate Charge ^c	Qg			11	17			
Gate-Source Charge ^c	Q _{gs}	V_{DS} = 30 V, V_{GS} = 10 V, I_D = 23 A		3		nC		
Gate-Drain Charge ^c	Q _{gd}			3				
Turn-On Delay Time ^c	t _{d(on)}			8	15			
Rise Time ^c	t _r	V_{DD} = 30 V, R_L = 1.3 Ω		15	25			
Turn-Off Delay Time ^c	t _{d(off)}	$\text{I}_\text{D}\cong$ 23 A, V_GEN = 10 V, R_g = 2.5 Ω		30	45	115		
Fall Time ^c	t _f			25	40			
Source-Drain Diode Ratings and Cha	aracteristics	(T _C = 25 °C)						
Pulsed Current	I _{SM}				50	А		
Diode Forward Voltage	V _{SD}	I _F = 15 A, V _{GS} = 0 V		1.0	1.5	V		
Reverse Recovery Time	t _{rr}	I _F = 15 A, di/dt = 100 A/μs		30	60	ns		

Notes:

a. For design aid only; not subject to production testing.

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

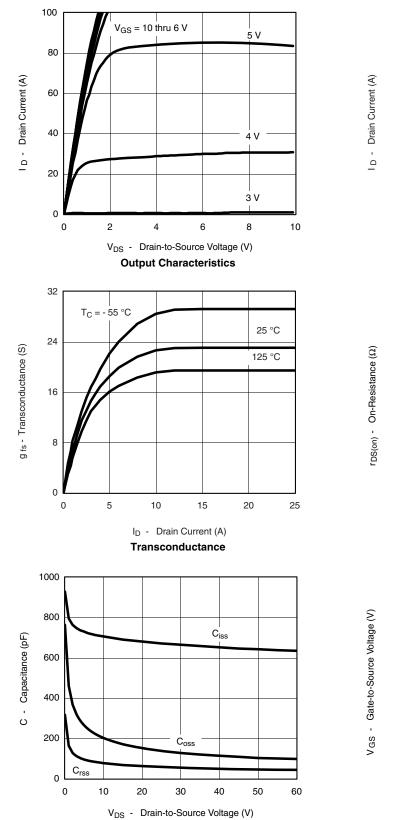
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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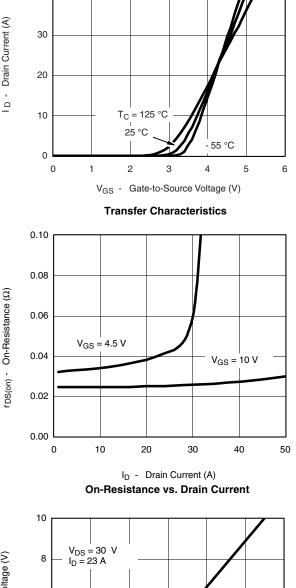
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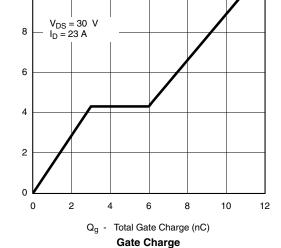
Capacitance

TYPICAL CHARACTERISTICS 25 °C unless noted



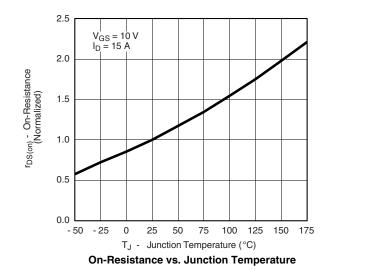
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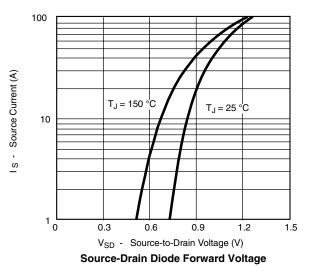
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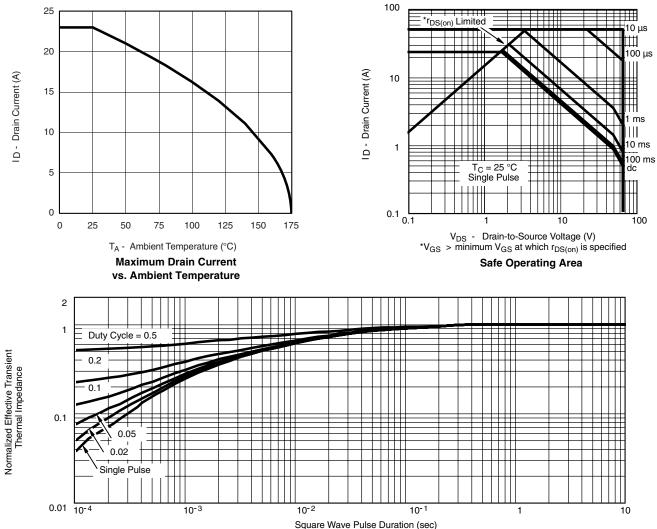
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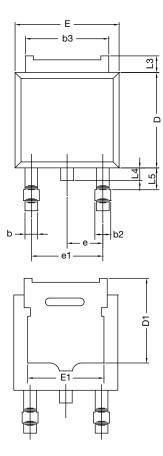
THERMAL RATINGS

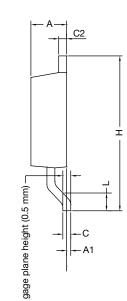


Square Wave Pulse Duration (sec) Normalized Thermal Transient Impedance, Junction-to-Case



TO-252AA CASE OUTLINE





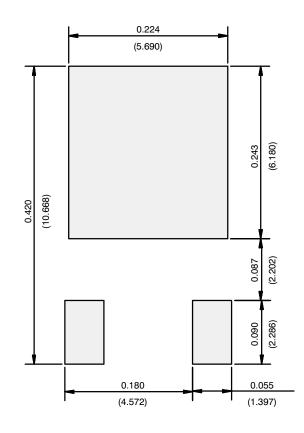
	MILLIN	IETERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090) BSC	
e1	4.56 BSC		0.180) BSC	
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	
ECN: X12- DWG: 534	0247-Rev. M, 7	24-Dec-12			

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)



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